1N5614 1N5620
1N5616 1N5622
1N5618

GLASS PASSIVATED
SILICON RECTIFIERS
1.0 AMP, 200 THRU 800 VOLT



GPR-1A CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 1N5614 series types are silicon rectifiers mounted in a hermetically sealed, glass passivated package, designed for general purpose applications where high reliability is desired.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T_A=25°C unless otherwise noted)

	SYMBOL	1N5614	1N5616	1N5618	1N5620	1N5622	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	200	400	600	800	1000	V
DC Blocking Voltage	V_R	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	140	280	420	560	700	V
Average Forward Current (T_A=55°C)	I_O			1.0			A
Peak Forward Surge Current, tp=8.3ms	I_{FSM}			40			A
Operating and Storage Junction Temperature	T_J, T_{stg}			-65 to +200			°C

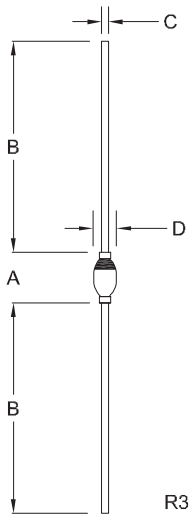
ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	V_R=Rated V_{RRM}		0.5	μA
I_R	V_R=Rated V_{RRM}, T_A=100°C		25	μA
BV_R	I_R=50μA (1N5614)	220		V
BV_R	I_R=50μA (1N5616)	440		V
BV_R	I_R=50μA (1N5618)	660		V
BV_R	I_R=50μA (1N5620)	880		V
BV_R	I_R=50μA (1N5622)	1100		V
V_F	I_F=1.0A		1.2	V
C_J	V_R=12V, f=130kHz		35	pF
t_{rr}	I_F=0.5A, I_R=1.0A, I_{rr}=0.25A		2.0	μs

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GPR-1A CASE - MECHANICAL OUTLINE



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	-	0.240	-	6.10
B	1.000	-	25.40	-
C	0.028	0.034	0.71	0.86
D	0.070	0.150	1.80	3.81

GPR-1A (REV: R3)

MARKING: FULL PART NUMBER